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Collean J. Dow

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit 2822

In re application of

Axel Brintzinger et al.

Serial No.: 09/873,537

J. , Q3/0/3,33/

Filed: June 4, 2001

Title: DUAL DAMASCENE ANTI-FUSE

WITH VIA BEFORE WIRE

November 14, 2002

Examiner: Monica Lewis

IBM Corporation Dept. 18G/Bldg, 300-482

2070 Route 52

Hopewell Junction, NY

12533-6531

Request for Reconsideration

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Commissioner for Patents and Trademarks Washington, D.C. 20231

NOV 1 4 2002

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Sir:

The following request for reconsideration is submitted in response to the office action dated August 14, 2002.

The invention centers on novel interconnect structures having an anti-fuse formed as a layer having openings that define via locations. The structures of the invention advantageously incorporate anti-fuses at reduced manufacturing cost.

Boardman et al. (US 5120679) discloses a structure where the vias are defined by holes in thick dielectric layer 46. The antifuse layer 52 is removed from all locations except for holes where the antifuses are desired. See Figures 3c-3f. Boardman et al. does not disclose or suggest an anti-fuse layer with an

opening which defines a via location.

Chang (US 5565703) discloses an antifuse structure where a dielectric layer 37) is deposited over the periphery of an antifuse layer 36 to define a location of a conductive plug 50. Chang does not disclose or suggest an anti-fuse layer with an opening which defines a via location.

Go et al. (US 5592016) discloses anti-fuse structures which are located above or below vias. Go et al. does not disclose or suggest an anti-fuse layer with an opening which defines a via location.

McCollum et al. (US 5770885) discloses a silicon oxynitride layer on a substrate over which an amorphous silicon anti-fuse is formed. McCollum et al. does not disclose or suggest an anti-fuse layer with an opening which defines a via location.

For the above reasons, applicants submit that the present claims are patentable over the prior art of record and that the application is in condition for allowance. Such allowance is earnestly and respectfully solicited.

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Respectfully submitted, Axel Brintzinger et al.

NOV 1 4 2002

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Steven Capella, Attorney

Reg. No. 33,086

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P.01/03

Docket No.

CERTIFICATE OF TAPPlicant(s): Axel Brintz	Docket No. FIS920000011US2		
Serial No. 09/873,537	Filing Date June 4, 2001	Examiner Monica Lewis	Group Art Unit 2822
Invention: DUAL DAMASCENE ANT	1-fuse with via before v	VIRE	
I hereby certify that this		Request for Reconsideration (Identify type of correspondence)	
is being facsimile transm	itted to the United States Paten	at and Trademark Office (Fax.	No. 703-872-9318
On November 14 (Date)	1, 2002. (3 pages	being sent via fax)	
	<u>.</u>	Colleen J. Dew (Typed or Printed Name of Person Signing Certificate) Colleon J. Day (Signature)	
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